

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A process comprising:
dicing a semiconductor wafer before forming devices on the semiconductor wafer, the dicing forming trenches in the semiconductor wafer;
back-grinding the semiconductor wafer after forming the devices on the semiconductor wafer;
scribing the trenches.
2. (Original) The process of claim 1 further comprising forming an oxide in the trenches formed by dicing the semiconductor wafer.
3. (Canceled)
4. (Currently Amended) The process of claim 2 ~~[[3]]~~ further comprising removing the oxide after the devices are formed on the semiconductor wafer.
5. (Original) The process of claim 1 wherein the dicing is performed by one of a group of processes consisting of sawing, etching, and lasering.
6. (Original) The process of claim 5 wherein the trenches extend 90 to 150 microns from the surface of the semiconductor wafer.

7. (Original) The process of claim 4 wherein the scribing is performed by using a laser.
8. (Currently Amended) A method comprising:
 ~~etching~~ scribing a plurality trenches in a surface of a semiconductor wafer
between a plurality of die on the semiconductor wafer, the trenches extending between
approximately 90 and 150 microns from the surface of the semiconductor wafer;
 back-grinding the opposite surface of the semiconductor to the bottom of the
trenches.
9. (Currently Amended) The method of claim 8 wherein the plurality of trenches are
scribed ~~etched~~ into the surface of the semiconductor wafer before devices are
completely formed on the plurality of die.
10. (Original) The method of claim 9 further comprising depositing oxide in the
plurality of trenches.
11. (Original) The process of claim 10 further comprising planarizing the oxide.
12. (Original)The process of claim 11 further comprising removing the oxide by
using a laser.

13. A method comprising:

singulating a plurality of die on a semiconductor wafer by creating a plurality of trenches extending approximately 90 to 150 microns from the surface of the semiconductor wafer before forming devices on the plurality of die;

back-grinding the semiconductor wafer to the bottom of the plurality of trenches;

scribing the plurality of trenches;

forming oxide in the plurality of trenches;

planarizing the oxide;

removing the oxide.

14. (Canceled)